

TO-92 Plastic-Encapsulate Transistors

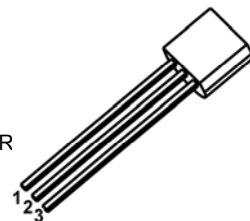
2SC1318 TRANSISTOR (NPN)

FEATURES

- Low Collector to Emitter Saturation Voltage $V_{CE(sat)}$
- Complementary Pair with 2SA720

TO - 92

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.01\text{mA}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.01\text{mA}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	85		340	
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=300\text{mA}, I_B=30\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=300\text{mA}, I_B=30\text{mA}$			1.5	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			15	pF
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=200\text{MHz}$		200		MHz

CLASSIFICATION OF $h_{FE(1)}$

RANK	Q	R	S
RANGE	85-170	120-240	170-340

